

Abstract of the Disclosure

A nonvolatile ferroelectric memory device having a multi-bit control function performs read/write operations
5 by selecting a plurality of cells simultaneously, thereby improving the operation speed of a chip. In the nonvolatile ferroelectric memory device, a plurality of cells are selected at the same time, and stable sensing values of data having a small distribution can be obtained
10 by using average characteristics of a plurality of selected cells. Accordingly, since two or more cells are simultaneously selected and a plurality of bits are read/written in the cells depending on stabilized charge, the operation speed of a chip can be improved.